

Supplementary Material

Magnetron Sputter-Deposited β -Ga₂O₃ Films on c-Sapphire Substrate: Effect of Rapid Thermal Annealing Temperature on Crystalline Quality

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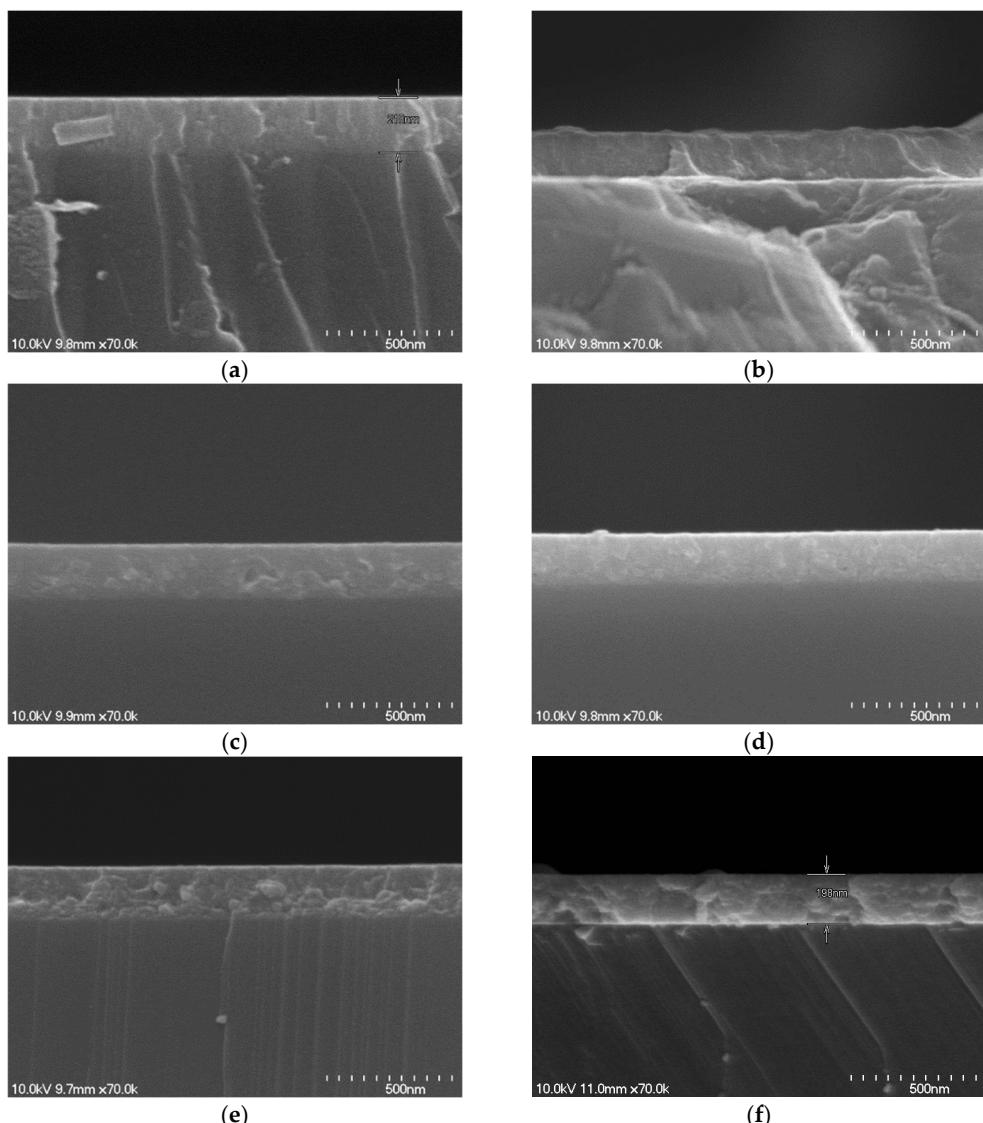


Figure S1. Cross-sectional field emission scanning electron microscope (FESEM) images of (a) as-deposited and annealed Ga₂O₃ films at different post-annealing temperatures: (b) 500, (c) 600, (d) 700, (e) 800, and (f) 900 °C.